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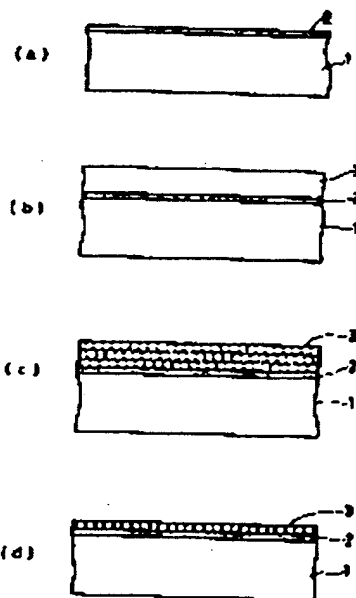
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## (54) FORMATION OF INSULATING FILM

### (57)Abstract:

**PURPOSE:** To form easily a thin insulating film at a uniform thickness by forming a thin film of a smectic liquid crystal on a substrate and crosslinking the same.

**CONSTITUTION:** This method is constituted of a stage for forming a smectic liquid crystal 3 in a smectic state on a substrate 1 in such a way that the surface thereof is made parallel with each layer of the liquid crystal 3, a stage for exerting the force in the direction intersecting orthogonally with the inter-layer arrangement direction on the liquid crystal 3 and forming the thin film of the liquid crystal 3 on the substrate 1 by utilizing the ease of the slip between the respective layers and a stage for crosslinking the liquid crystal 3 formed into the thin film. An orienting material layer 2 is preferably provided preliminarily on the substrate and the liquid crystal is coated in the liquid state thereon and is slowly cooled in the stage for forming the liquid crystal 3. The liquid crystal may be formed after the orienting material is mixed with the liquid crystal. The upper layer side of the liquid crystal is stripped by, for example, the centrifugal force of a spinner, and the extremely thin layer is formed to a uniform thickness in the stage for forming the thin film. The liquid crystal is then crosslinked and the secure insulating film is obtd.



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